

FORM PTO-1449 SAMUELS, GAUTHIER, STEVENS LLP
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Eugene A. Fitzgerald
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TTN	AA	5,208,182	5/4/93	Narayan et al.			11/12/91
TTN	AB	5,252,173	10/12/93	Inoue			11/22/91
TTN	AC	5,279,687	01/18/94	Tuppen et al.			02/27/90
TTN	AD	6,117,750	09/12/00	Bensahel et al.			12/21/98
TTN	AE	5,210,052	05/11/93	Takasaki			05/13/92
TTN	AF	5,221,413	06/22/93	Brasen et al.			04/24/91
TTN	AG	5,308,444	05/03/94	Fitzgerald, Jr. et al.			05/28/93
TTN	AH	5,442,205	08/15/95	Brasen et al.			09/09/93
TTN	AI	5,810,924	09/22/98	Legoues et al.			06/07/95
TTN	AJ	6,107,653	08/22/00	Fitzgerald			06/23/98

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
TTN	AK	63073398 ✓	3/29/88	Japan			yes (abstract)
	AL						
	AM						
	AN						
	AO						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
TTN	AP ✓	"Relaxed Ge _x Si _{1-x} structures for III-V integration with Si and high mobility two-dimensional electron gases in Si"; by Fitzgerald et al. 1992 American Vacuum society; pages 1807-1819
TTN	AQ ✓	"GeSi/Si NANOSTRUCTURES" by E.A. Fitzgerald; Department of Materials Science, Massachusetts Institute of Technology (1995) pgs; 1-15

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ATTORNEY DOCKET NO.

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TTN	AA 4,900,372	02/13/1990	Lee et al.	148	33.4	03/02/1989
	AB					
	AC					
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	AG					
	AH					
	AI					
	AJ					

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AK					
	AL					
	AM					
	AN					
	AO					

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
TTN	AP	Hsin-Chiao Luan et al., "High-quality Ge epilayers on Si with low threading-dislocation densities," <i>Applied Physics Letters</i> , American Institute of Physics, New York, Vol. 75, No. 19, November 8, 1999, pages 2909-2911.
	AQ	

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